

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A method for manufacturing a semiconductor device comprising:

- forming a semiconductor film over an insulating surface;
- forming an oxide film on the semiconductor film;
- radiating the semiconductor film with a first laser beam using a lens;
- radiating the semiconductor film with a second laser beam after radiating with the first laser beam; and
- radiating the semiconductor film with a third laser beam after radiating with the second laser beam,

wherein a wavelength of the second laser beam and a wavelength of the third laser beam are different from a wavelength of the first laser beam.

2. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 1, wherein a crystallized semiconductor film is formed after radiating the semiconductor film with the first laser beam.

3. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 1, wherein the oxide film on the semiconductor film is removed after radiating the semiconductor film with the second laser beam.

4. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 1, wherein a surface of the semiconductor film is level after radiating the semiconductor film with the second laser beam.

5. (Canceled)

6. (Original) The method for manufacturing the semiconductor device according to Claim 1, wherein an energy density of the first laser beam is 300 to 500mJ/cm².

7. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film over an insulating surface;

forming an oxide film on the semiconductor film;

radiating the semiconductor film with a first laser beam;

radiating the semiconductor film with a second laser beam after radiating with the first laser beam under an atmosphere comprising at least one of hydrogen and an inert gas; and

radiating the semiconductor film with a third laser beam after radiating with the second laser beam;

wherein a wavelength of the second laser beam and a wavelength of the third laser beam are different from a wavelength of the first laser beam.

8. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 7, wherein a crystallized semiconductor film is formed after radiating the semiconductor film with the first laser beam.

9. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 7, wherein the oxide film on the semiconductor film is removed after radiating the semiconductor film with the second laser beam.

10. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 7, wherein a surface of the semiconductor film is level after radiating the semiconductor film with the second laser beam.

11. (Canceled)

12. (Original) The method for manufacturing the semiconductor device according to Claim 7, wherein an energy density of the first laser beam is 300 to 500mJ/cm².

13. (Previously Presented) A method for manufacturing a semiconductor device comprising:

- forming a semiconductor film over an insulating surface;
- forming an oxide film on the semiconductor film;
- radiating the semiconductor film with a first laser beam;
- radiating the semiconductor film with a second laser beam after radiating with the first laser beam; and
- radiating the semiconductor film with a third laser beam after radiating with the second laser beam under an atmosphere comprising at least one of hydrogen and an inert gas, wherein a wavelength of the second laser beam and a wavelength of the third laser beam are different from a wavelength of the first laser beam.

14. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 13, wherein a crystallized semiconductor film is formed after radiating the semiconductor film with the first laser beam.

15. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 13, wherein the oxide film on the semiconductor film is removed after radiating the semiconductor film with the second laser beam.

16. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 13, wherein a surface of the semiconductor film is level after radiating the semiconductor film with the second laser beam.

17. (Canceled)

18. (Original) The method for manufacturing the semiconductor device according to Claim 13, wherein an energy density of the first laser beam is 300 to 500mJ/cm².

19. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film over an insulating surface;

forming an oxide film on the semiconductor film;

radiating the semiconductor film with a first laser beam;

radiating the semiconductor film with a second laser beam after radiating with the first laser beam; and

radiating the semiconductor film with a third laser beam after radiating with the second laser beam,

wherein a pulse width of the second laser beam is smaller than a pulse width of the first laser beam, and

wherein a wavelength of the second laser beam and a wavelength of the third laser beam are different from a wavelength of the first laser beam.

20. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 19, wherein a crystallized semiconductor film is formed after radiating the semiconductor film with the first laser beam.

21. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 19, wherein the oxide film on the semiconductor film is removed after radiating the semiconductor film with the second laser beam.

22. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 19, wherein a surface of the semiconductor film is level after radiating the semiconductor film with the second laser beam.

23. (Canceled)

24. (Original) The method for manufacturing the semiconductor device according to Claim 19, wherein an energy density of the first laser beam is 300 to 500mJ/cm².

25. (Previously Presented) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film over an insulating surface;

forming an oxide film on the semiconductor film;

radiating the semiconductor film with a first laser beam;

radiating the semiconductor film with a second laser beam after radiating with the first laser beam; and

radiating the semiconductor film with a third laser beam after radiating with the second laser beam,

wherein an energy of the third laser beam is higher than an energy of the first laser beam, and

wherein a wavelength of the second laser beam and a wavelength of the third laser beam are different from a wavelength of the first laser beam.

26. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 25, wherein a crystallized semiconductor film is formed after radiating the semiconductor film with the first laser beam.

27. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 25, wherein the oxide film on the semiconductor film is removed after radiating the semiconductor film with the second laser beam.

28. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 25, wherein a surface of the semiconductor film is level after radiating the semiconductor film with the second laser beam.

29. (Canceled)

30. (Original) The method for manufacturing the semiconductor device according to Claim 25, wherein an energy density of the first laser beam is 300 to 500mJ/cm².

31. (Previously Presented) A method for manufacturing a semiconductor device comprising:

- forming a semiconductor film over an insulating surface;
 - forming an oxide film on the semiconductor film;
 - crystallizing the semiconductor film by a heat treatment to form a crystallized semiconductor film;
 - radiating the crystallized semiconductor film with a first laser beam;
 - radiating the crystallized semiconductor film with a second laser beam after radiating with the first laser beam; and
 - radiating the crystallized semiconductor film with a third laser beam after radiating with the second laser beam,
- wherein a wavelength of the second laser beam and a wavelength of the third laser beam are different from a wavelength of the first laser beam.

32. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 31, wherein a crystallized semiconductor film having improved crystal characteristics is formed after radiating the semiconductor film with the first laser beam.

33. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 31, wherein the oxide film on the crystallized semiconductor film is removed after radiating the crystallized semiconductor film with the second laser beam.

34. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 31, wherein a surface of the crystallized semiconductor film is level after radiating the crystallized semiconductor film with the second laser beam.

35. (Canceled)

36. (Original) The method for manufacturing the semiconductor device according to Claim 31, wherein an energy density of the first laser beam is 300 to 500mJ/cm².

37. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 1, wherein the first laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

38. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 1, wherein the second laser beam is one selected from the group consisting of an excimer laser, ArF laser, and a KrF laser.

39. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 1, wherein the third laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

40. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 7, wherein the first laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

41. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 7, wherein the second laser beam is one selected from the group consisting of an excimer laser, ArF laser, and a KrF laser.

42. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 7, wherein the third laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

43. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 13, wherein the first laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

44. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 13, wherein the second laser beam is one selected from the group consisting of an excimer laser, ArF laser, and a KrF laser.

45. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 13, wherein the third laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

46. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 19, wherein the first laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

47. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 19, wherein the second laser beam is one selected from the group consisting of an excimer laser, ArF laser, and a KrF laser.

48. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 19, wherein the third laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

49. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 25, wherein the first laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

50. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 25, wherein the second laser beam is one selected from the group consisting of an excimer laser, ArF laser, and a KrF laser.

51. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 25, wherein the third laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

52. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 31, wherein the first laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

53. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 31, wherein the second laser beam is one selected from the group consisting of an excimer laser, ArF laser, and a KrF laser.

54. (Previously Presented) The method for manufacturing the semiconductor device according to Claim 31, wherein the third laser beam is one selected from the group consisting of an excimer laser, Nd:YAG laser, and a YLF laser.

55.-98. (Canceled)

99. (Previously presented) The method for manufacturing the semiconductor device according to claim 7, wherein the inert gas is selected from the group consisting of nitrogen, argon, helium, neon, krypton and xenon.

100. (Previously Presented) The method for manufacturing the semiconductor device according to claim 13, wherein the inert gas is selected from the group consisting of nitrogen, argon, helium, neon, krypton and xenon.